MOSFET

OptiMOS™ Small-Signal-Transistor, 100 V

PG-SOT23-3

Features

- N-channel
- Enhancement mode
- Logic level (4.5V rated)
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Fully qualified according to JEDEC for Industrial Applications

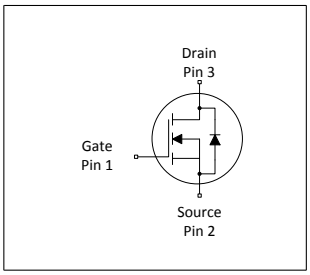


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$, V_{GS}=10 V	6	Ω
$R_{DS(on),max}$, V_{GS}=4.5 V	10	Ω
I_D	0.19	A
ESD Sensitivity, JESD22-A114 (HBM)	class 0 (<250V)	

Type / Ordering Code	Package	Marking	Related Links
BSS123I	PG-SOT23	AIs	-

Table of Contents

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	- -	- -	0.19 0.15	A	V_{GS}=10 V, T_A=25 °C V_{GS}=4.5 V, T_A=70 °C
Pulsed drain current	$I_{D,pulse}$	-	-	0.77	A	T_A=25 °C
Avalanche energy, single pulse	E_{AS}	-	-	2.0	mJ	I_D=0.19 A, R_{GS}=25 Ω
Reverse diode dv/dt	dv/dt	-	-	6	kV/µs	I_D=0.19 A, V_{DS}=80 V, di/dt=200 A/µs, $T_{j,max}$=150 °C
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation[1]	P_{tot}	-	-	0.5	W	T_A=25 °C, R_{THJA}=250 °C/W
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - ambient, minimum footprint[1]	R_{thJA}	-	-	250	K/W	-

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	V_{GS}=0 V, I_D=250 µA
Gate threshold voltage	$V_{GS(th)}$	0.8	1.4	1.8	V	V_{DS}=V_{GS}, I_D=13 µA
Zero gate voltage drain current	I_{DSS}	- -	- -	0.01 5	µA	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	-	10	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	2.4 2.7	6 10	Ω	V_{GS}=10 V, I_D=0.19 A V_{GS}=4.5 V, I_D=0.15 A
Transconductance	g_{fs}	-	0.41	-	S	|V_{DS}|≥2|I_D|$R_{DS(on)max}$, I_D=0.15 A

[1] Performed on 40mm² FR4 PCB. The traces are 1mm wide, 70µm thick and 20mm long; they are present on both sides of the PCB

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	15	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance	C_{oss}	-	2.5	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Reverse transfer capacitance	C_{rss}	-	1.6	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	2.3	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=0.19 A, $R_{G,ext}$=6 Ω
Rise time	t_r	-	3.2	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=0.19 A, $R_{G,ext}$=6 Ω
Turn-off delay time	$t_{d(off)}$	-	7.4	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=0.19 A, $R_{G,ext}$=6 Ω
Fall time	t_f	-	22	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=0.19 A, $R_{G,ext}$=6 Ω

Table 6 Gate charge characteristics

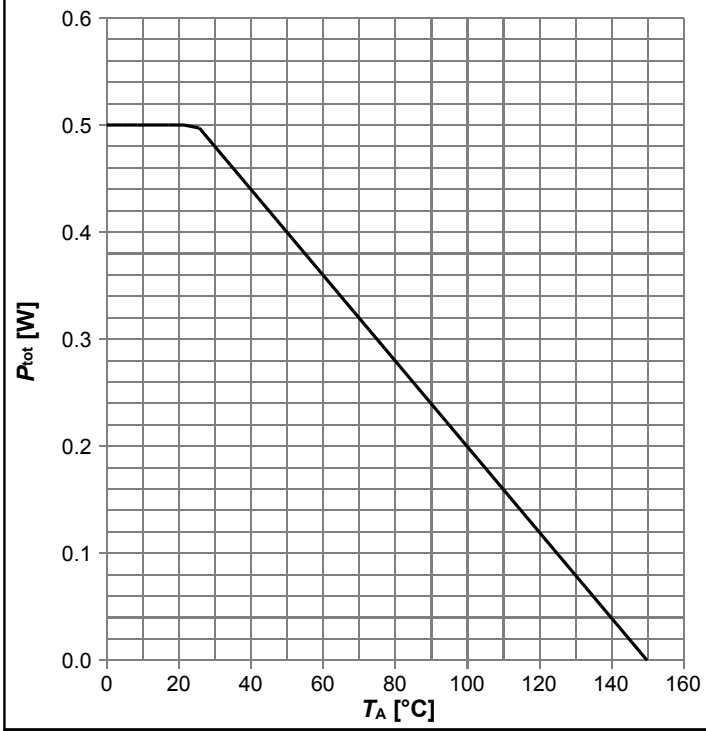
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	0.04	-	nC	V_{DD}=50 V, I_D=0.19 A, V_{GS}=0 to 10 V
Gate to drain charge	Q_{gd}	-	0.23	-	nC	V_{DD}=50 V, I_D=0.19 A, V_{GS}=0 to 10 V
Gate charge total	Q_g	-	0.63	-	nC	V_{DD}=50 V, I_D=0.19 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	2.5	-	V	V_{DD}=50 V, I_D=0.19 A, V_{GS}=0 to 10 V

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	0.19	A	T_A=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	0.77	A	T_A=25 °C
Diode forward voltage	V_{SD}	-	0.86	1.1	V	V_{GS}=0 V, I_F=0.19 A, T_j=25 °C
Reverse recovery time	t_{rr}	-	12	18	ns	V_R=50 V, I_F=0.19 A, di_F/dt=100 A/µs
Reverse recovery charge	Q_{rr}	-	4.3	6.5	nC	V_R=50 V, I_F=0.19 A, di_F/dt=100 A/µs

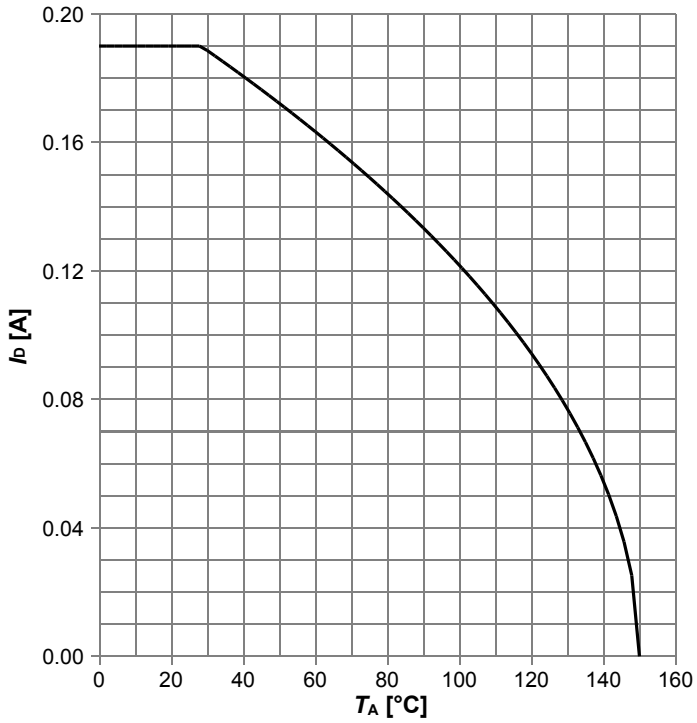
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



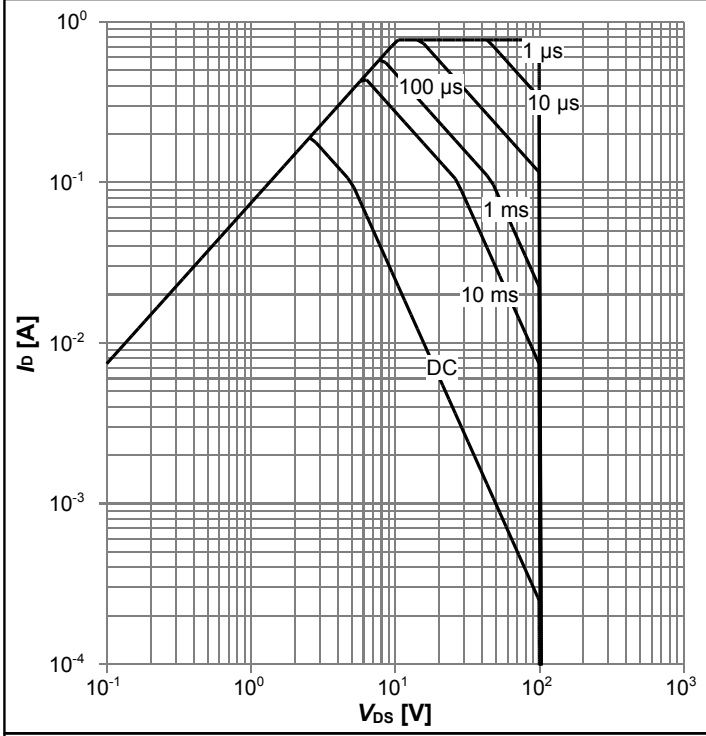
P_{tot}=f(T_A)

Diagram 2: Drain current



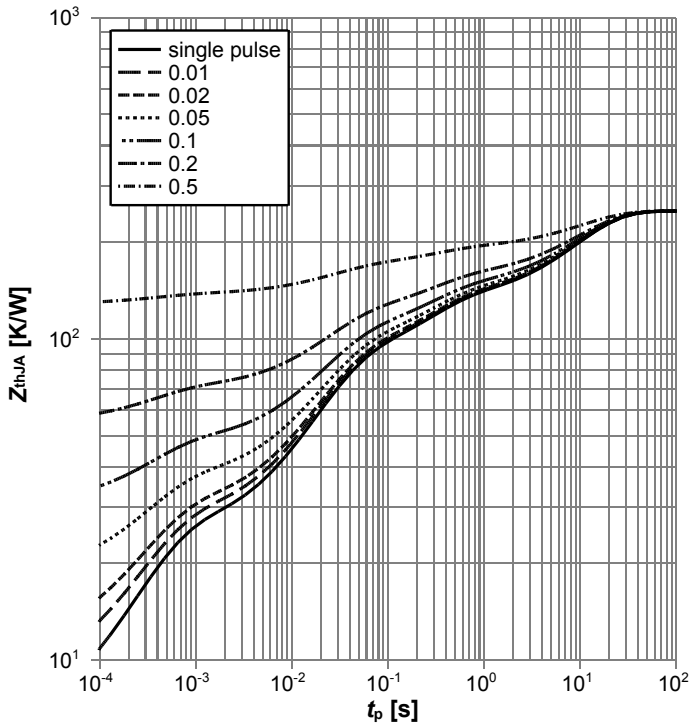
I_D=f(T_A); V_{GS}≥10 V

Diagram 3: Safe operating area



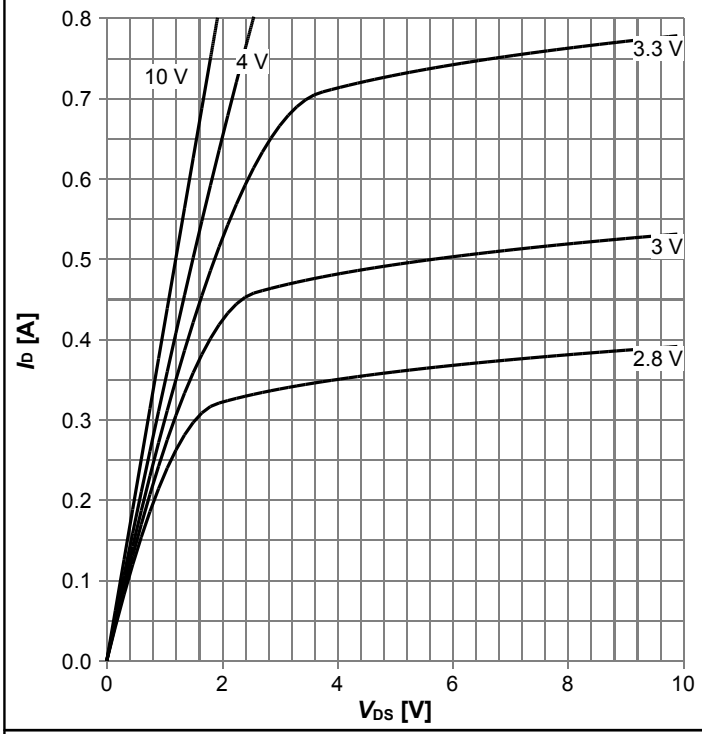
I_D=f(V_{DS}); T_A=25 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



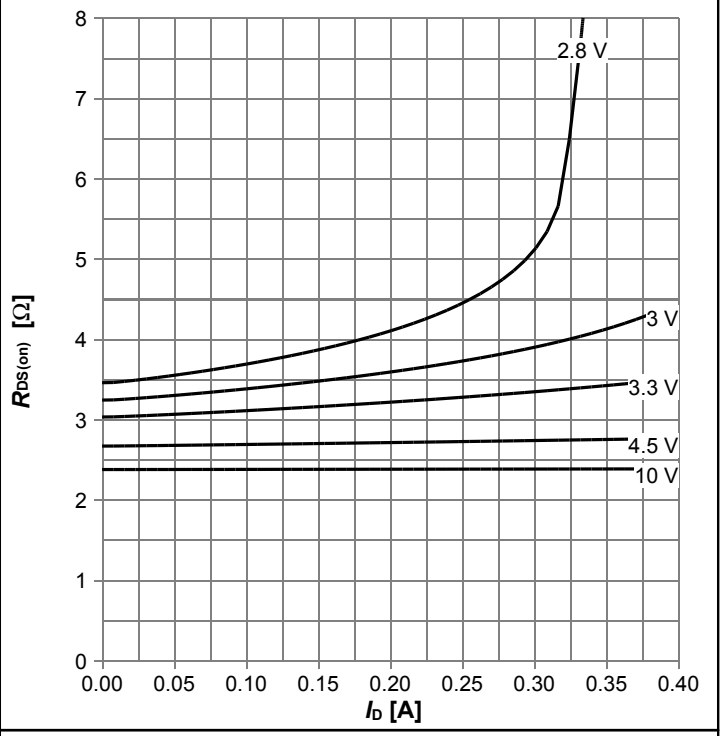
Z_{thJA}=f(t_p); parameter: D=t_p/T

Diagram 5: Typ. output characteristics



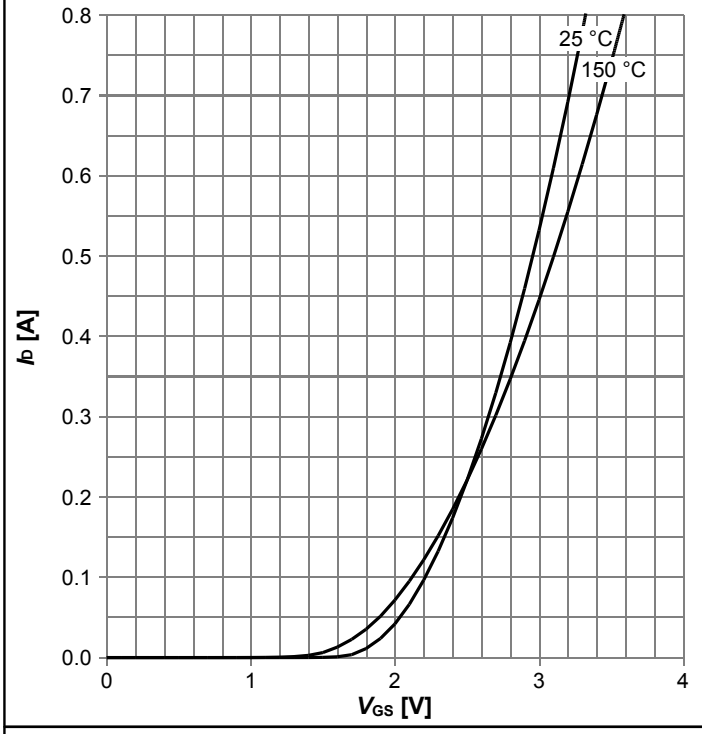
I_D=f(V_{DS}), T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



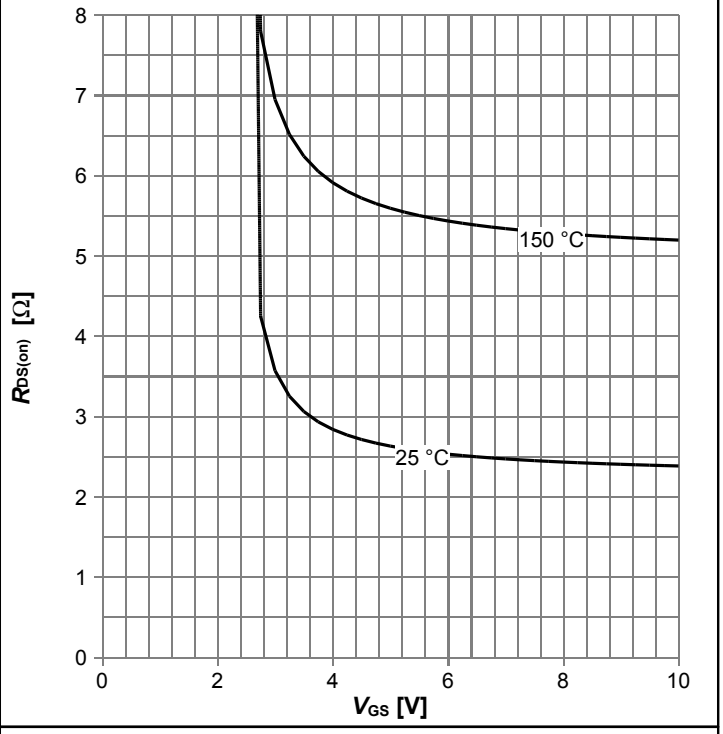
$R_{DS(on)}$=f(I_D), T_j=25 °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



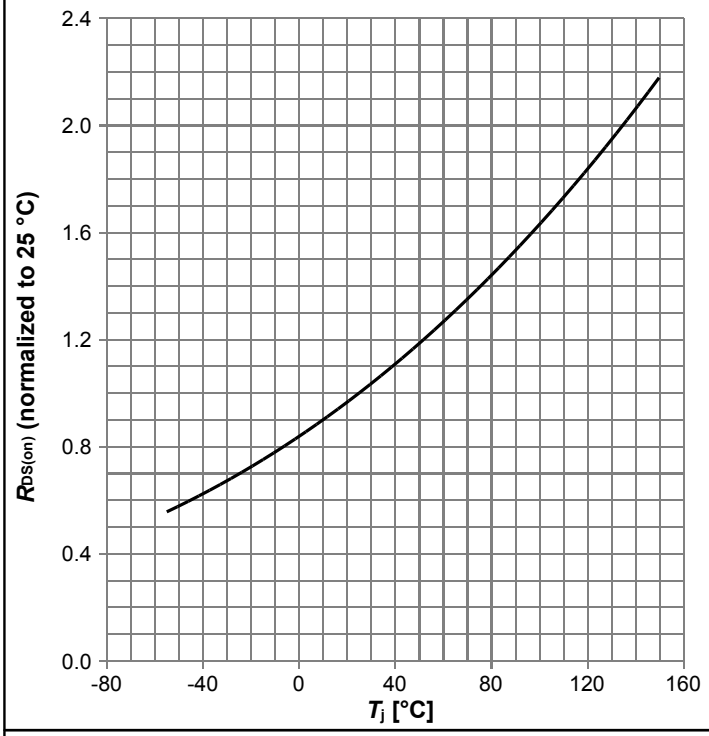
I_D=f(V_{GS}), |V_{DS}|>2|I_D|$R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



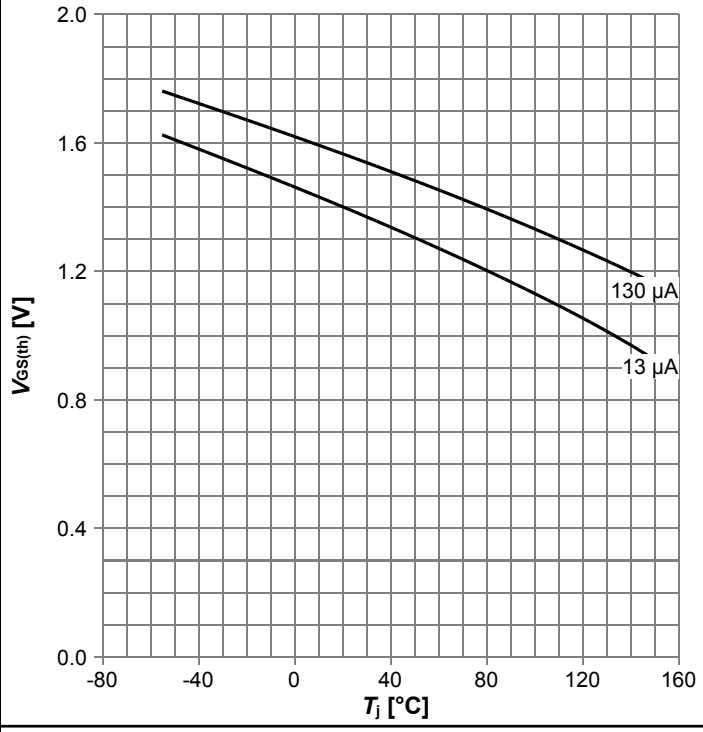
$R_{DS(on)}$=f(V_{GS}), I_D=0.19 A; parameter: T_j

Diagram 9: Normalized drain-source on resistance



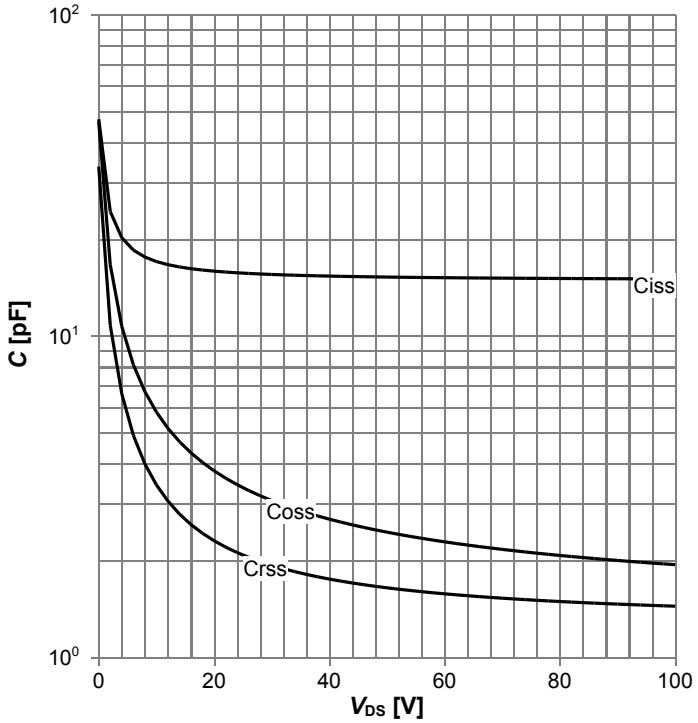
$R_{DS(on)}$=f(T_j), I_D=0.19 A, V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



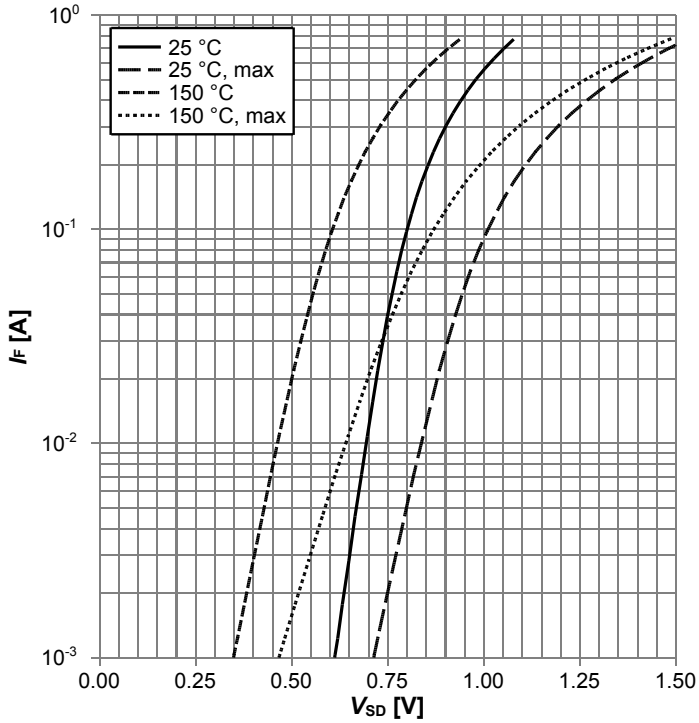
$V_{GS(th}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



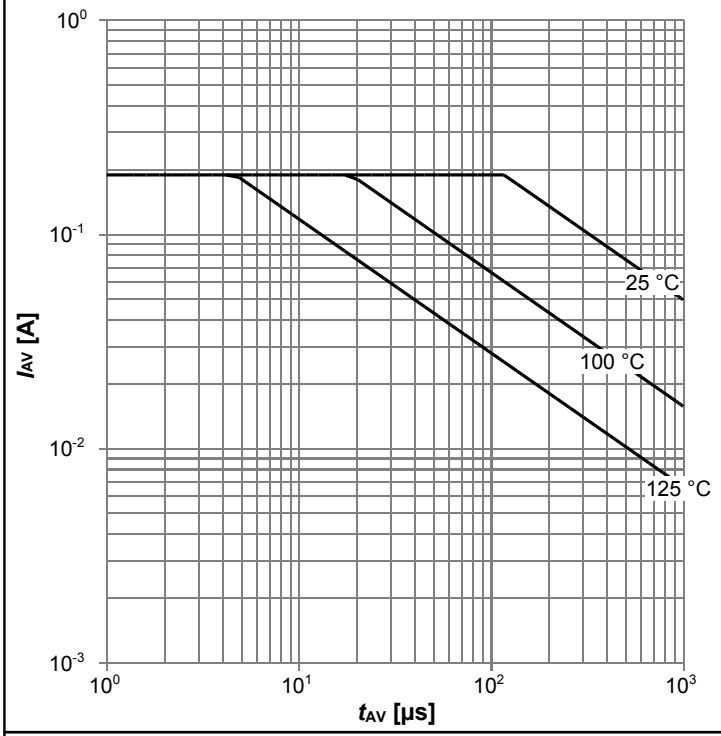
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



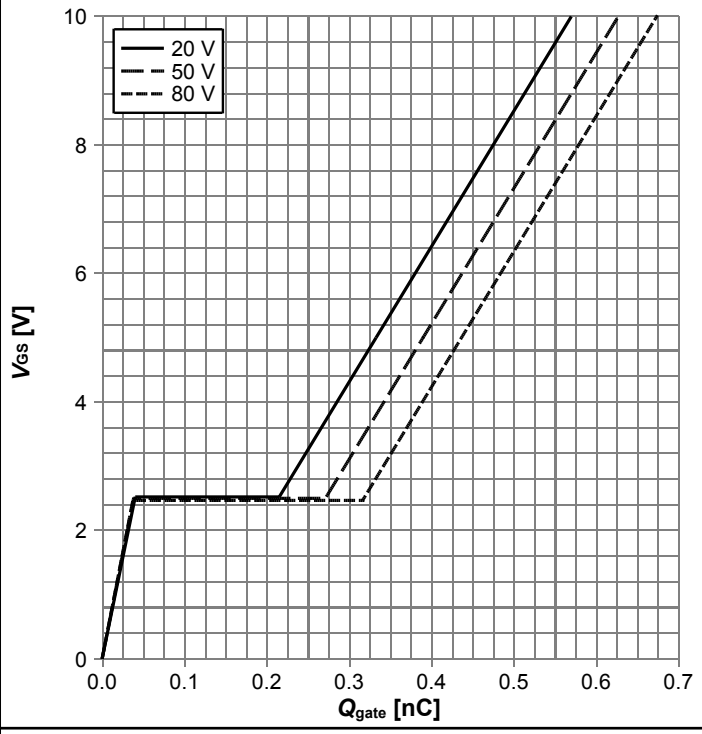
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



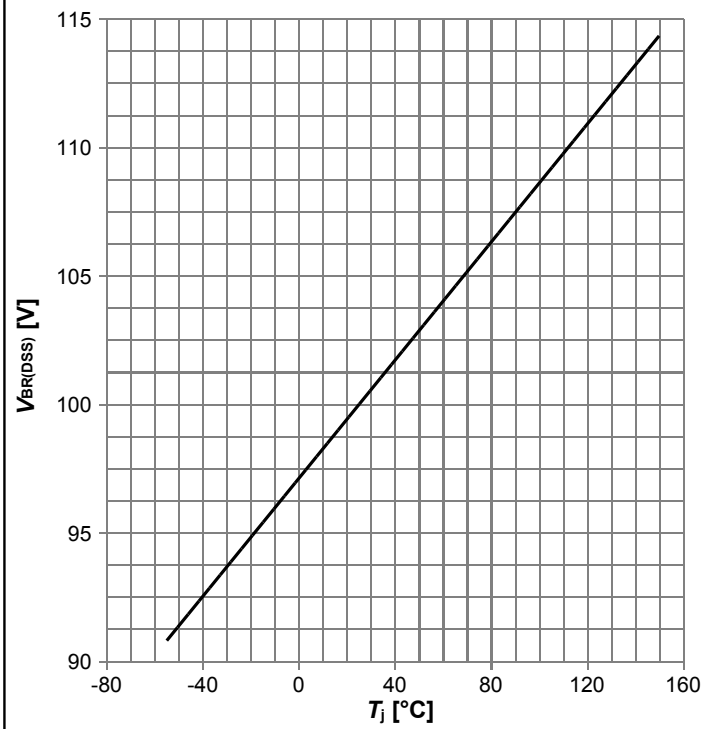
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



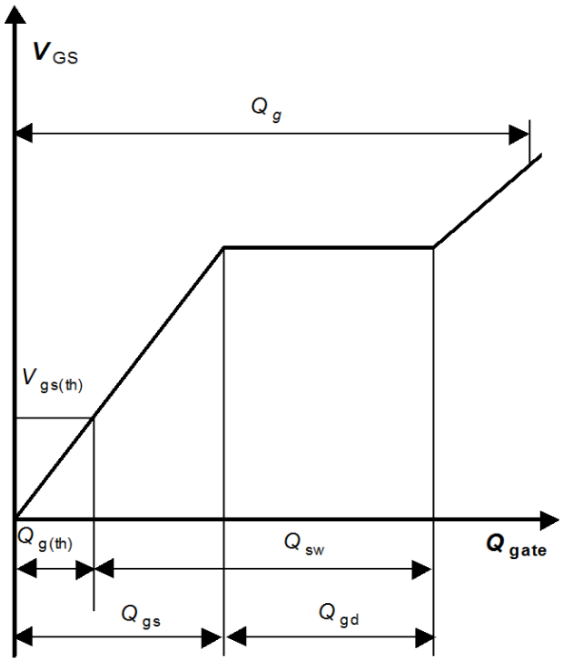
V_{GS}=f(Q_{gate}), I_D=0.19 A pulsed, T_j=25 °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

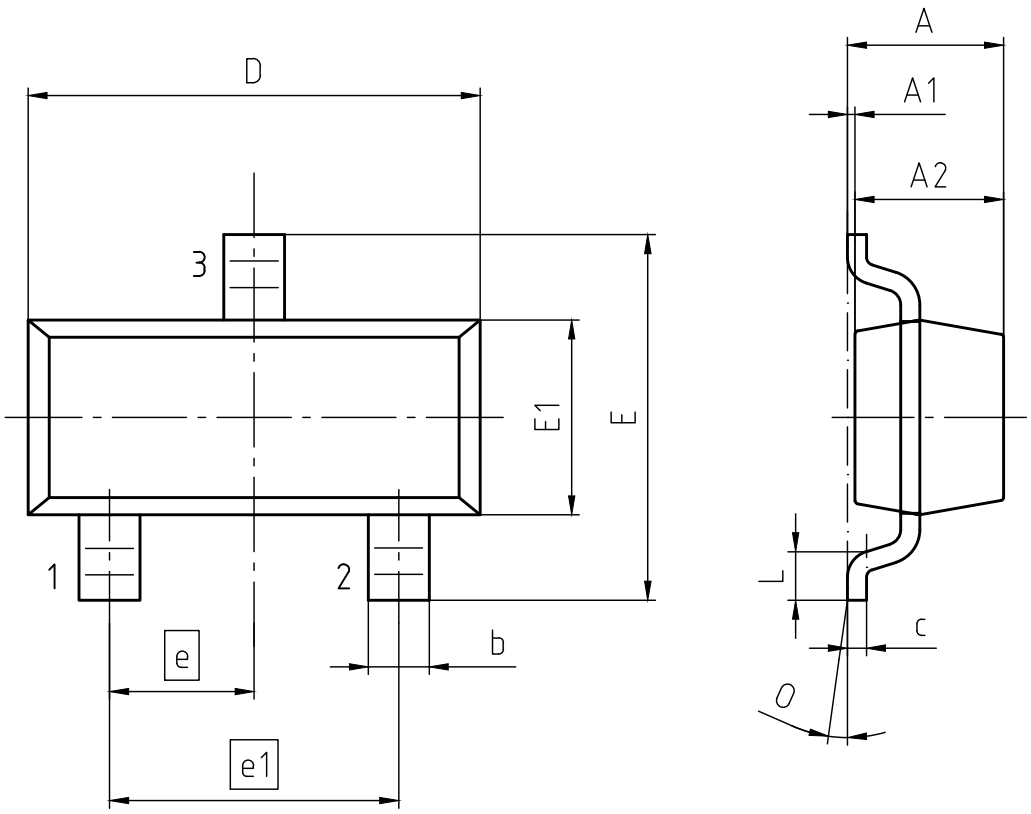


$V_{BR(DSS)}$=f(T_j); I_D=250 µA

Diagram Gate charge waveforms



5 Package Outlines



PACKAGE - GROUP NUMBER:	PG-SOT23-3-U01	
REVISION: 01	DATE: 09.12.2020	
DIMENSIONS	**MILLIMETERS**	
	MIN.	MAX.
A	0.89	1.12
A1	0.01	0.10
A2	0.88	1.02
b	0.30	0.50
c	0.08	0.20
D	2.80	3.04
E	2.10	2.64
E1	1.20	1.40
e	0.95	
e1	1.90	
L	0.15	0.60
O	0°	8°

Figure 1 Outline PG-SOT23, dimensions in mm

Revision History

BSS123I

Revision: 2021-02-01, Rev. 2.1

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.0	2021-01-26	Release of final version
2.1	2021-02-01	Update format

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